

ISOCOM COMPONENTS

Photo Transistor - Safety Approvals, VDE 0884, BSI, SETI and UL (continued) *Note 1

Part Number	Features	Current Transfer Ratio Min (%)	CTR Test Conditions	Isolation Test Voltage KV	Continuous Forward Current Max (mA)	BV _{CEO} I _C = 1mA Min (V)	I _{CEO} (Dark) V _{CE} = 10V Max (nA)	V _{CE} (Sat) Max (V)	Schematic No.	Package No.
SFH600-0	Optically Coupled pair with Infrared Emitter and Photo Transistor Detector	40 - 80	I _F = 10mA V _{CE} = 5V	2.8 rms	60	70	35	0.4 (I _F = 10mA) (I _C = 2.5mA)	5	2
SFH600-1		63 - 125								
SFH600-2		100 - 200								
SFH600-3		160 - 320								
SFH600-4		200 - 400								
SFH601-1	Base Lead Connected	40 - 80	I _F = 10mA V _{CE} = 5V	5.3 d.c.	60	70	50	0.4 (I _F = 10mA) (I _C = 2.5mA)	5	2
SFH601-2		63 - 125								
SFH601-3		100 - 200								
SFH601-4		160 - 320								
SFH601-5		200 - 400								

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CNX82A	Optically Coupled pair with Infrared Emitter and Photo Transistor Detector	40	I _F = 10mA V _{CE} = 0.4V	5.3 d.c.	60	50	50	0.4 (I _F = 10mA) (I _C = 4mA)	8	2
CNY17F-1		40 - 80	I _F = 10mA V _{CE} = 5V	4.4 d.c.		70		0.4 (I _F = 10mA) (I _C = 2.5mA)		
CNY17F-2		63 - 125								
CNY17F-3		100 - 200								
CNY17F-4	160 - 320	Base Lead Not Connected	I _F = 10mA V _{CE} = 10V	7.5 d.c.	30	50	0.4 (I _F = 10mA) (I _C = 2.5mA)			
MOC8101	50 - 80									
MOC8102	73 - 117									
MOC8103	108 - 173									
MOC8104	160 - 256									
MOC8111	20									
MOC8112	50									
MOC8113	100			5.3 pk			0.4 (I _F = 10mA) (I _C = 0.5mA)			
IS205	100									
IS206	50									

* Note 1: To obtain a product tested to the above four safety approvals add "X" after basic type number e.g. 4N35X.
To obtain 10mm lead spread add suffix "G" after full type number e.g. 4N35XG.

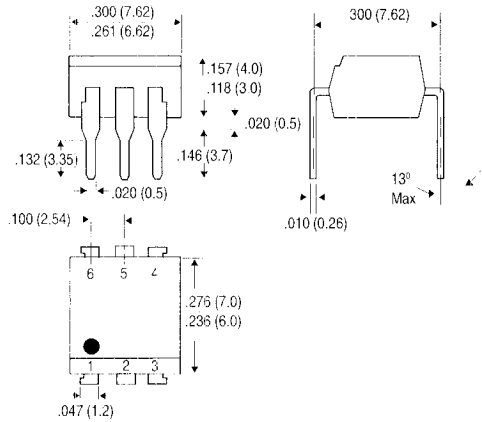
FET Couplers

Single Channel DIP, FET Couplers

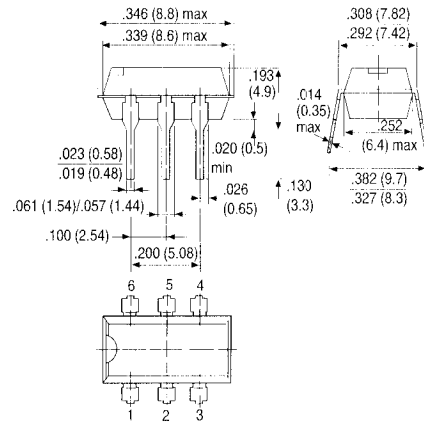
Part Number	Features	Isolation Breakdown Voltage Min (RMS)	On State Resistance I _F = 16mA I _{AS} = ±100μA Max (Ω)	Output Breakdown Voltage I _{AS} = ±10μA Max (V)	Continuous Forward Current Max (mA)	Off State current I _{AS} = ±15V Max (nA)	Schematic No.	Package No.
H11F1	Optically Coupled pair with Infrared LED Emitter and a Symmetrical Bilateral Silicon Photo Detector	2500	200	30	60	50	10	6
H11F2			330					
H11F3			470					
IS610			200					
IS611		5000	170					

Coupler Package Drawings

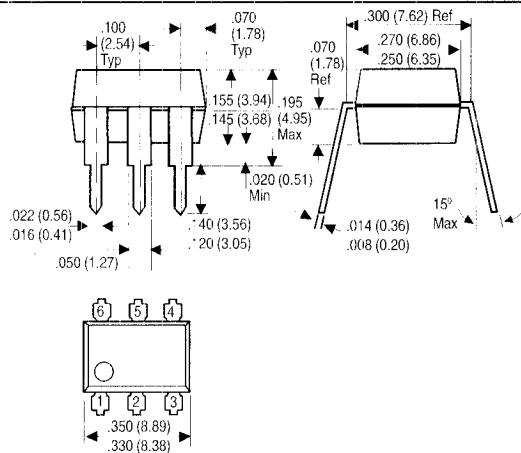
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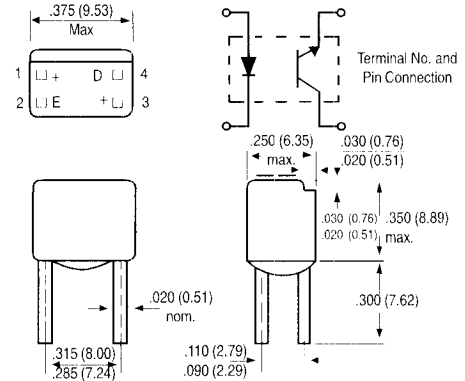
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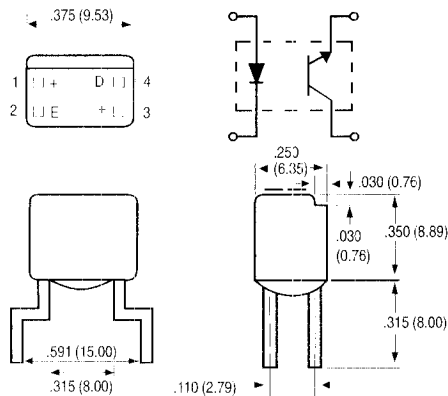
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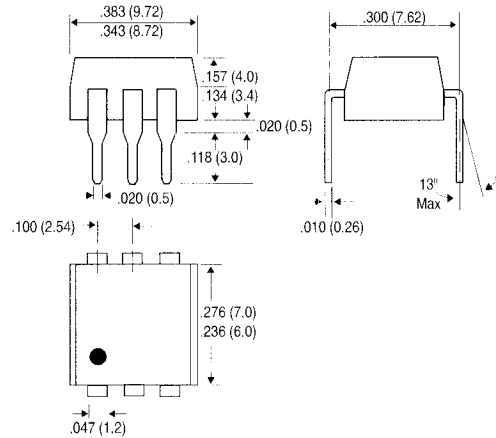
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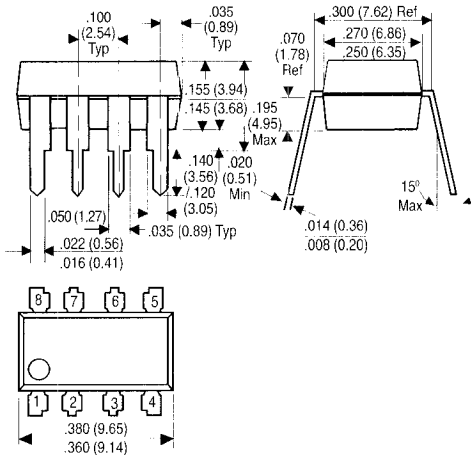
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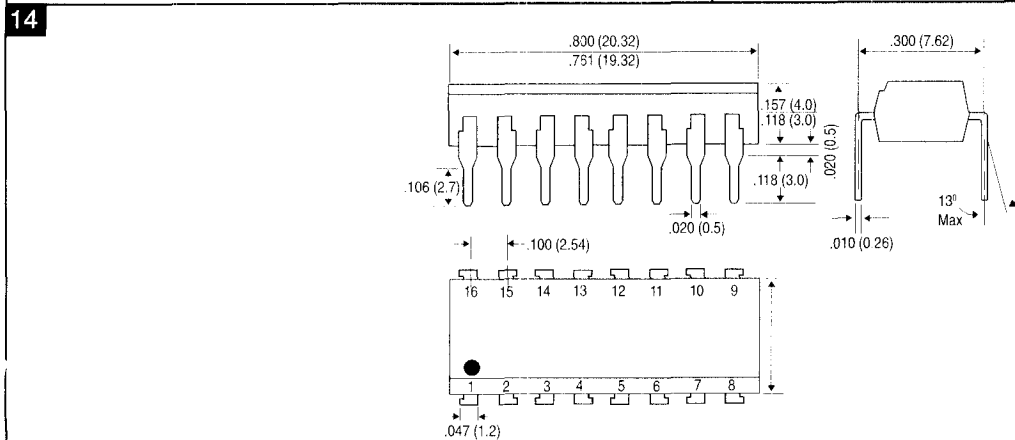
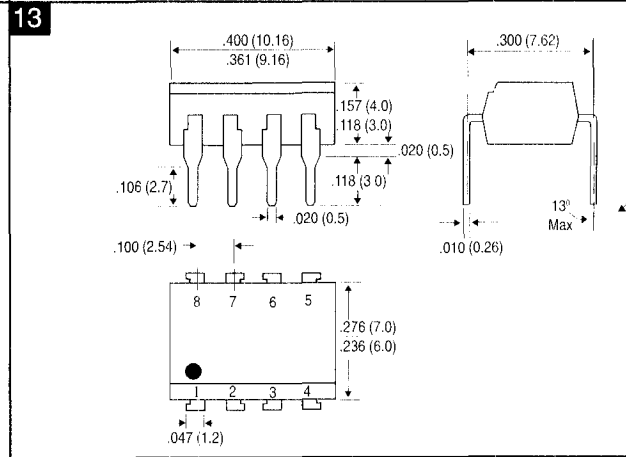
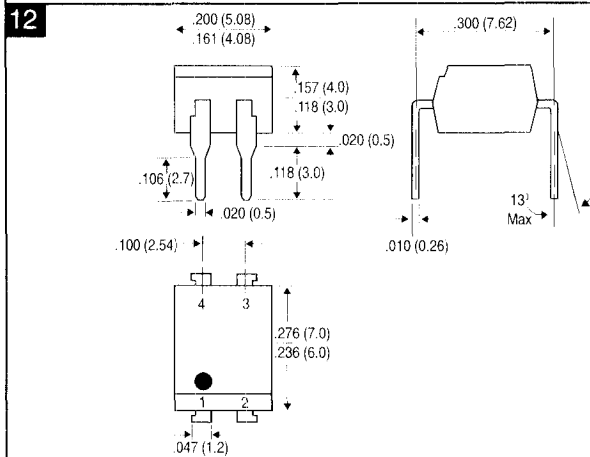
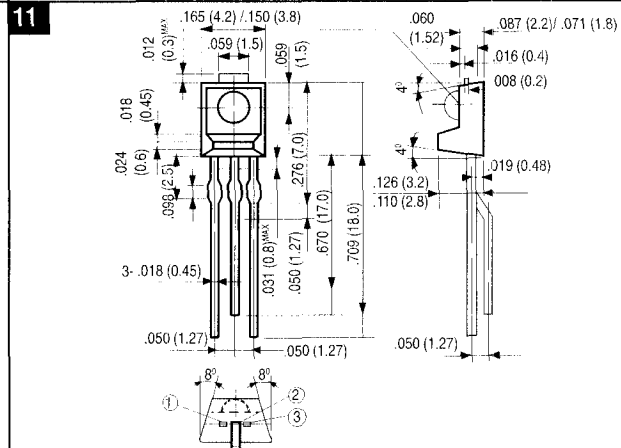
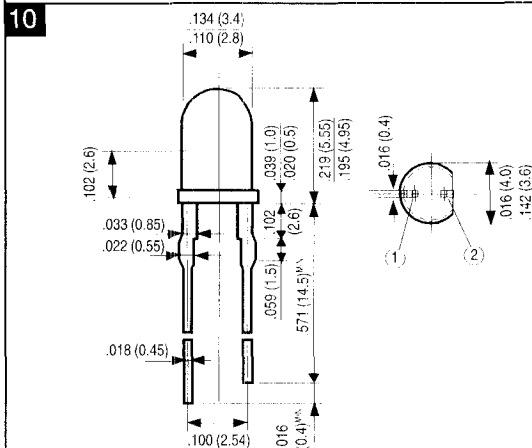
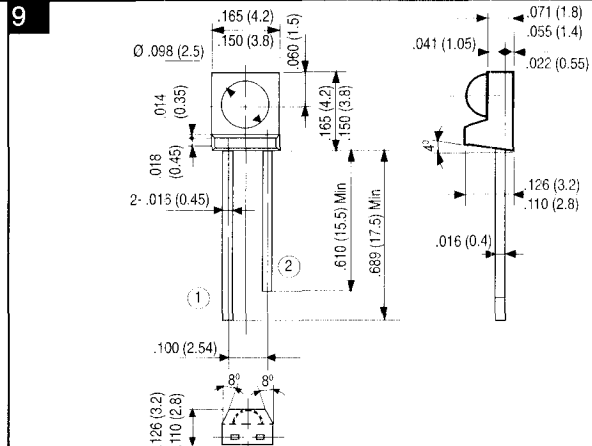
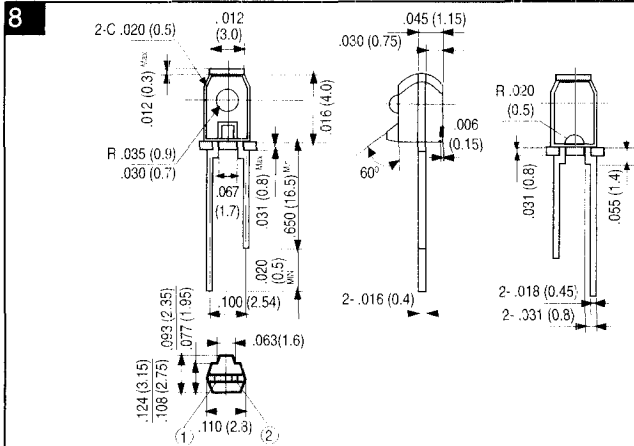
6



7



Coupler Package Drawings



Coupler Schematics

